

/ Descriptions

Silicon PNP transistor in a TO-92LM Plastic Package.

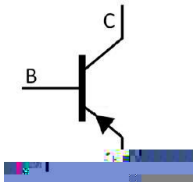
/ Features

High transition frequency, small collector output capacitance complementary pair with 2SC2705.

/ Applications

Audio frequency amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

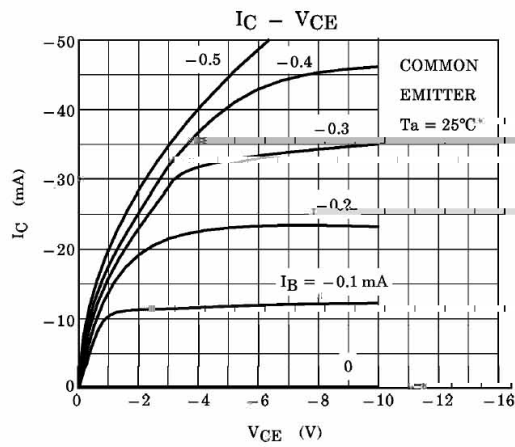
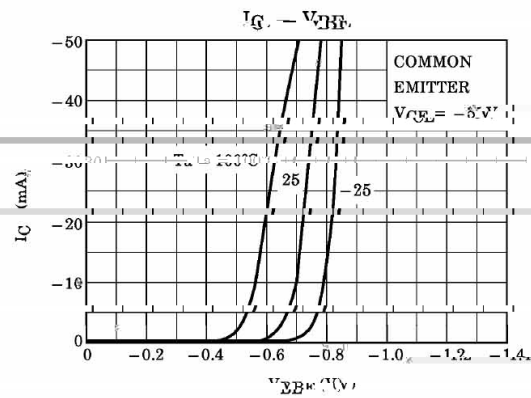
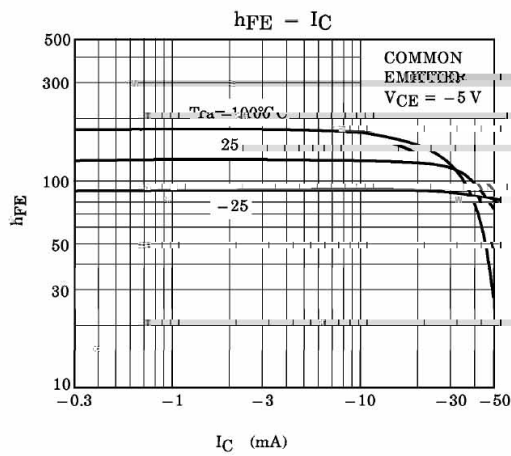
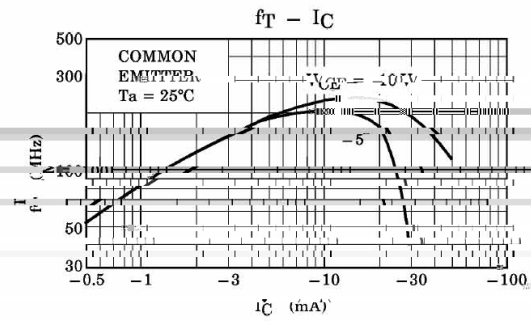
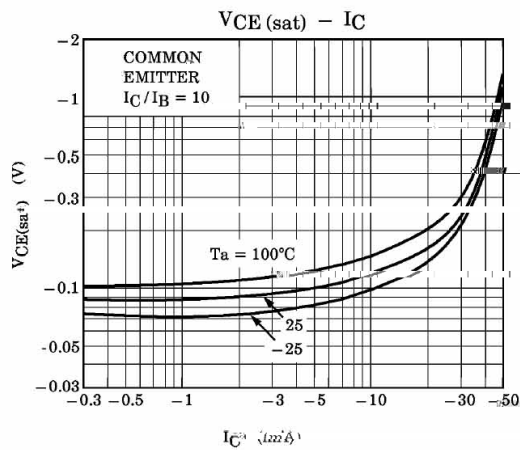
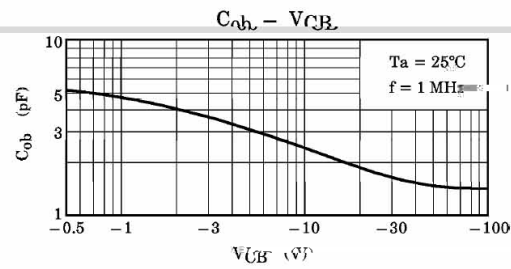
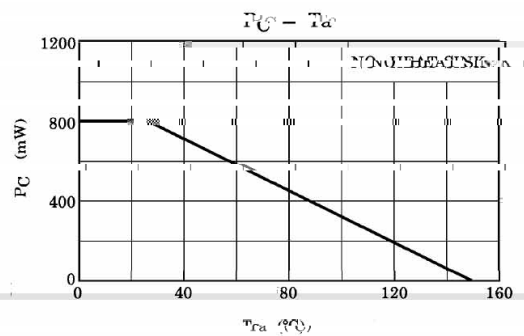
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	80~160	120~240

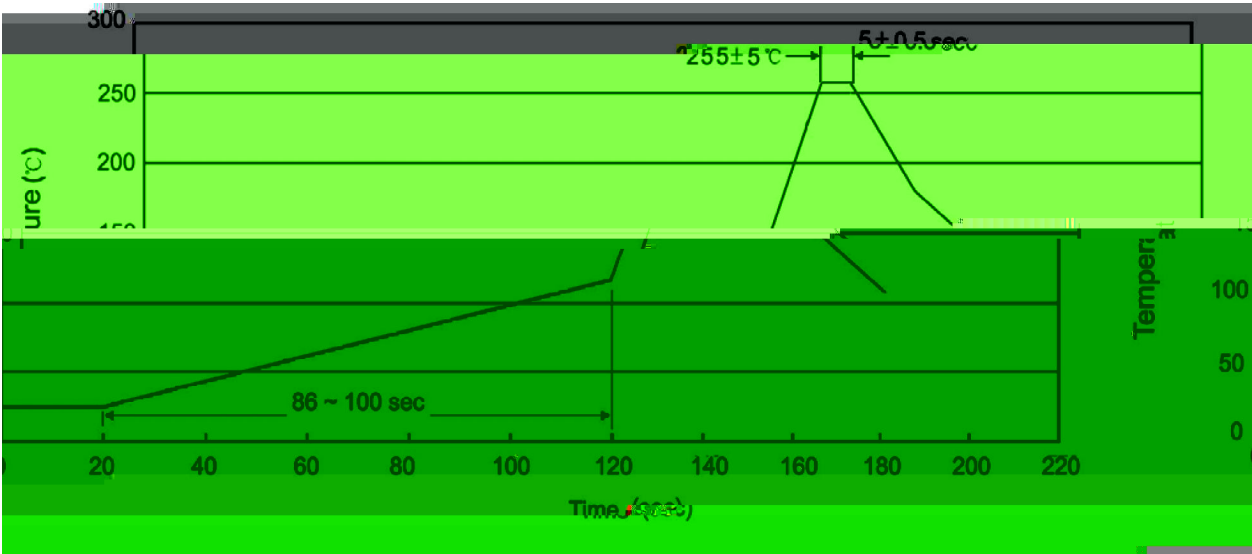
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-150	V
Collector to Emitter Voltage	V_{CEO}	-150	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-50	mA
Base Current	I_B	-5.0	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-150			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -150V$ $I_E = 0$			-0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-0.1	A
DC Current Gain	h_{FE}	$V_{CE} = -5.0V$ $I_C = -10mA$	80		240	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA$ $I_B = -1.0mA$			-1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE} = -5.0V$ $I_C = -10mA$			-0.8	V
Transition Frequency	f	$I_C = -10mA$ $V_{CE} = -5.0V$		200		MHz
Collector output capacitance	$C_{f=1.0MHz}$	$V_{CB} = -10V$ $I_E = 0$	2.5	pF		

/ Electrical Characteristic Curve



() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5

10 1 sec.

Temp.:270 5

Time:10 1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm3)
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